IN THE CLAIMS:

Claims 1-29 have been amended herein. All of the pending claims 1 through 29 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A method for forming a protective layer on a plurality of semiconductor device components, comprising:

providing a fabrication substrate carrying a plurality of semiconductor device components, adjacent semiconductor device components on ~~said~~ the fabrication substrate being separated from one another by a street extending therebetween;

applying a protective material to active surfaces of at least ~~said~~ the adjacent semiconductor device components;

severing ~~said~~ the protective material and at least partially severing ~~said~~ the adjacent semiconductor device components from one another along ~~said~~ the street; and

healing cracks and delaminated areas in ~~said~~ the protective ~~layer~~ material formed during ~~said~~ the at least partially severing.

2. (Currently Amended) The method of claim 1, wherein ~~said~~ providing comprises providing a fabrication substrate with at least one bond pad exposed at an active surface of each of ~~said~~ the adjacent semiconductor device components.

3. (Currently Amended) The method of claim 2, wherein ~~said~~ providing comprises providing a fabrication substrate with a plurality of semiconductor device components comprising at least one of semiconductor devices, interposers, and carrier substrates.

4. (Currently Amended) The method of claim 2, wherein ~~said~~ applying comprises applying ~~said~~ the protective material such that ~~said~~ the at least one bond pad of each of ~~said~~ the

plurality of semiconductor device components is exposed through ~~said~~ the protective material sufficiently to effect electrical contact therewith.

5. (Currently Amended) The method of claim 2, wherein ~~said~~ providing comprises providing ~~said~~ the fabrication substrate with each of ~~said~~ the plurality of semiconductor device components having a conductive structure protruding from ~~said~~ the at least one bond pad thereof.

6. (Currently Amended) The method of claim 5, wherein ~~said~~ applying comprises applying ~~said~~ the protective material such that ~~said~~ the protective material contacts a base portion of at least one ~~said~~ conductive structure.

7. (Currently Amended) The method of claim 6, wherein ~~said~~ applying comprises forming a support structure around ~~said~~ the base portion of ~~said~~ the at least one conductive structure.

8. (Currently Amended) The method of claim 5, wherein ~~said~~ applying comprises applying ~~said~~ the protective material such that ~~said~~ the protective material is spaced apart from a base portion of at least one ~~said~~ conductive structure.

9. (Currently Amended) The method of claim 1, wherein ~~said~~ applying comprises applying a preformed sheet of protective material to ~~said~~ the active surfaces.

10. (Currently Amended) The method of claim 9, wherein ~~said~~ applying ~~said~~ the preformed sheet comprises applying a preformed sheet comprising partially cured protective material.

11. (Currently Amended) The method of claim 9, wherein ~~said~~ applying ~~said~~ the preformed sheet comprises applying a preformed sheet comprising thermoplastic material.

12. (Currently Amended) The method of claim 9, wherein ~~said~~ applying ~~said~~ preformed sheet comprises applying a preformed sheet including apertures positioned to align with ~~said~~ the at least one bond pad of each of ~~said~~ the adjacent semiconductor device components.

13. (Currently Amended) The method of claim 2, wherein ~~said~~ applying comprises applying a preformed sheet of protective material to ~~said~~ the active surfaces.

14. (Currently Amended) The method of claim 13, wherein ~~said~~ applying ~~said~~ the preformed sheet comprises applying a preformed sheet comprising partially cured protective material.

15. (Currently Amended) The method of claim 13, wherein ~~said~~ applying ~~said~~ the preformed sheet comprises applying a preformed sheet comprising thermoplastic material.

16. (Currently Amended) The method of claim 13, wherein ~~said~~ applying ~~said~~ the preformed sheet comprises applying a preformed sheet including apertures therein positioned to align with ~~said~~ the at least one bond pad of each of ~~said~~ the adjacent semiconductor device components.

17. (Currently Amended) The method of claim 13, wherein ~~said~~ applying ~~said~~ the preformed sheet comprises applying ~~said~~ the preformed sheet such that ~~said~~ a conductive structure protruding from each of ~~said~~ the adjacent semiconductor device components on ~~said~~ the fabrication substrate ~~pass~~ passes through a plane of ~~said~~ the preformed sheet.

18. (Currently Amended) The method of claim 17, further comprising heating each ~~said~~ conductive structure prior to applying ~~said~~ the preformed sheet.

19. (Currently Amended) The method of claim 1, wherein ~~said~~ applying comprises applying ~~said~~ the protective material in a liquid state.

20. (Currently Amended) The method of claim 19, further comprising spreading ~~said~~ the protective material to form a protective layer on ~~said~~ the active surfaces.

21. (Currently Amended) The method of claim 20, wherein ~~said~~ applying ~~said~~ the protective material in ~~said~~ the liquid state comprises applying a quantity of a substantially uncured polymer to ~~said~~ the active surfaces.

22. (Currently Amended) The method of claim 21, further comprising partially curing ~~said~~ the polymer prior to ~~said~~ severing and ~~said~~ at least partially severing.

23. (Currently Amended) The method of claim 22, wherein ~~said~~ healing is effected while ~~said~~ the polymer remains in a partially cured state.

24. (Currently Amended) The method of claim 23, further comprising further curing ~~said~~ the polymer following ~~said~~ healing.

25. (Currently Amended) The method of claim 24, further comprising completely severing ~~said~~ the adjacent semiconductor device components from one another along ~~said~~ the street following ~~said~~ healing.

26. (Currently Amended) The method of claim 20, wherein ~~said~~ applying ~~said~~ the protective material in ~~said~~ the liquid state comprises applying liquefied thermoplastic material to ~~said~~ the active surfaces.

27. (Currently Amended) The method of claim 26, further comprising permitting or causing ~~said~~ the thermoplastic material to at least partially harden prior to ~~said~~ severing and ~~said~~ at least partially severing.

28. (Currently Amended) The method of claim 26, wherein ~~said~~ healing comprises heating at least portions of ~~said~~ the thermoplastic material located over peripheral regions of ~~said~~ the adjacent semiconductor device components following ~~said~~ severing and ~~said~~ at least partially severing.

29. (Currently Amended) The method of claim 27, further comprising completely severing ~~said~~ the adjacent semiconductor device components from one another along ~~said~~ the street following ~~said~~ healing.